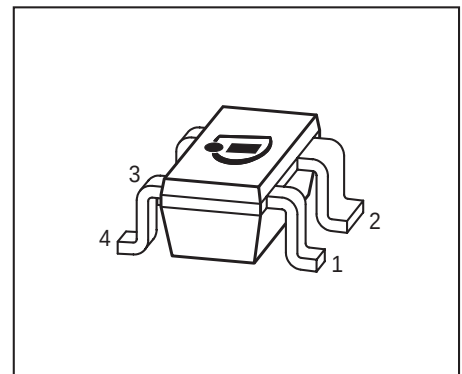


NPN Silicon RF Transistor*

- For low noise, high-gain broadband amplifiers at collector currents from 1 mA to 20 mA
- $f_T = 8$ GHz, $F = 0.9$ dB at 900 MHz
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101

* Short term description



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFP182R	RGs	1=E	2=C	3=E	4 = B	-	-	SOT143R

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	12	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	35	mA
Base current	I_B	4	
Total power dissipation ²⁾ $T_S \leq 69$ °C	P_{tot}	250	mW
Junction temperature	T_j	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ³⁾	R_{thJS}	≤ 325	K/W

¹Pb-containing package may be available upon special request

² T_S is measured on the collector lead at the soldering point to the pcb

³For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}$, $I_B = 0$	$V_{(BR)CEO}$	12	-	-	V
Collector-emitter cutoff current $V_{CE} = 20\text{ V}$, $V_{BE} = 0$	I_{CES}	-	-	100	μA
Collector-base cutoff current $V_{CB} = 10\text{ V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1\text{ V}$, $I_C = 0$	I_{EBO}	-	-	1	μA
DC current gain- $I_C = 10\text{ mA}$, $V_{CE} = 8\text{ V}$, pulse measured	h_{FE}	70	100	140	-

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 15\text{ mA}$, $V_{CE} = 8\text{ V}$, $f = 500\text{ MHz}$	f_T	6	8	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded	C_{cb}	-	0.25	0.4	pF
Collector emitter capacitance $V_{CE} = 10\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded	C_{ce}	-	0.3	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded	C_{eb}	-	0.8	-	
Noise figure $I_C = 3\text{ mA}$, $V_{CE} = 6\text{ V}$, $Z_S = Z_{Sopt}$, $f = 900\text{ MHz}$ $I_C = 3\text{ mA}$, $V_{CE} = 6\text{ V}$, $Z_S = Z_{Sopt}$, $f = 1.8\text{ GHz}$	F	- -	0.9 1.3	- -	dB
Power gain, maximum stable ¹⁾ $I_C = 10\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 900\text{ MHz}$	G_{ms}	-	22	-	dB
Power gain, maximum available ²⁾ $I_C = 10\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$	G_{ma}	-	16.5	-	dB
Transducer gain $I_C = 10\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\ \Omega$, $f = 900\text{ MHz}$ $I_C = 10\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\ \Omega$, $f = 1.8\text{ GHz}$	$ S_{21e} ^2$	- -	18 12	- -	dB

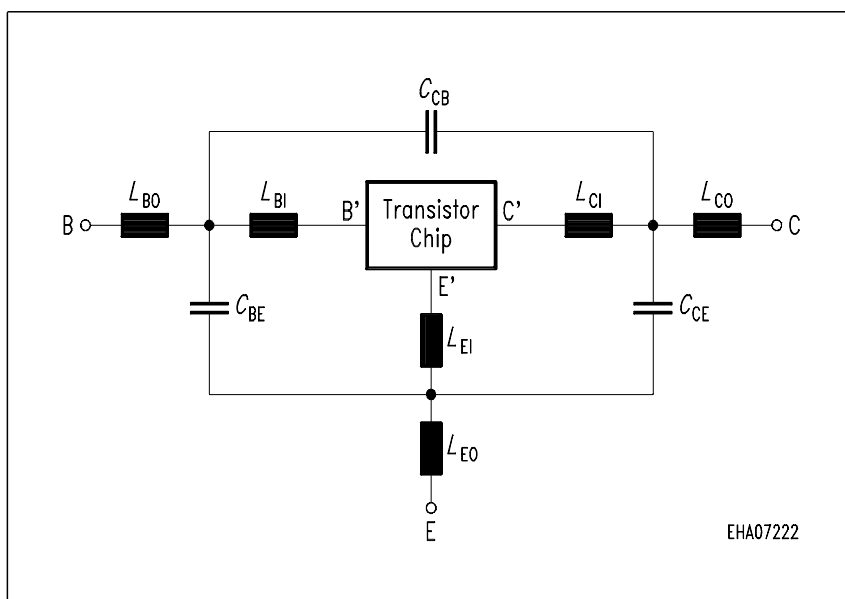
$$^1G_{ms} = |S_{21} / S_{12}|$$

$$^2G_{ma} = |S_{21e} / S_{12e}| (k - (k^2 - 1)^{1/2})$$

SPICE Parameter (Gummel-Poon Model, Berkley-SPICE 2G.6 Syntax):
Transistor Chip Data:

IS =	4.8499	fA	BF =	84.113	-	NF =	0.56639	-
VAF =	21.742	V	IKF =	0.14414	A	ISE =	8.4254	fA
NE =	0.91624	-	BR =	10.004	-	NR =	0.54818	-
VAR =	2.2595	V	IKR =	0.039478	A	ISC =	5.9438	fA
NC =	0.5641	-	RB =	3.4217	Ω	IRB =	0.071955	mA
RBM =	2.8263	Ω	RE =	2.1858	-	RC =	1.8159	Ω
CJE =	8.8619	fF	VJE =	1.0378	V	MJE =	0.40796	-
TF =	22.72	ps	XTF =	0.43147	-	VTF =	0.34608	V
ITF =	6.5523	mA	PTF =	0	deg	CJC =	490.25	fF
VJC =	1.0132	V	MJC =	0.31068	-	XCJC =	0.19281	-
TR =	1.7541	ns	CJS =	0	fF	VJS =	0.75	V
MJS =	0	-	XTB =	0	-	EG =	1.11	eV
XTI =	3	-	FC =	0.64175		TNOM	300	K

All parameters are ready to use, no scaling is necessary. Extracted on behalf of Infineon Technologies AG by:
Institut für Mobil- und Satellitentechnik (IMST)

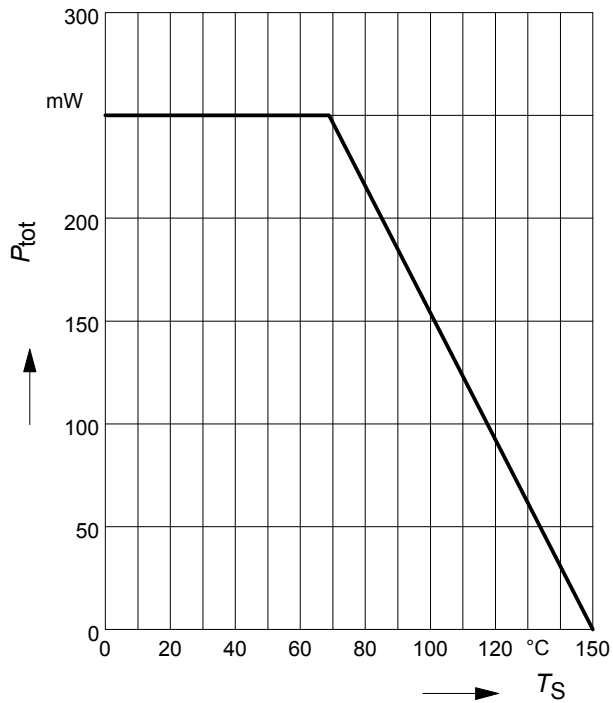
Package Equivalent Circuit:


L_{BI} =	0.89	nH
L_{BO} =	0.73	nH
L_{EI} =	0.4	nH
L_{EO} =	0.15	nH
L_{CI} =	0	nH
L_{CO} =	0.42	nH
C_{BE} =	189	fF
C_{CB} =	15	fF
C_{CE} =	187	fF

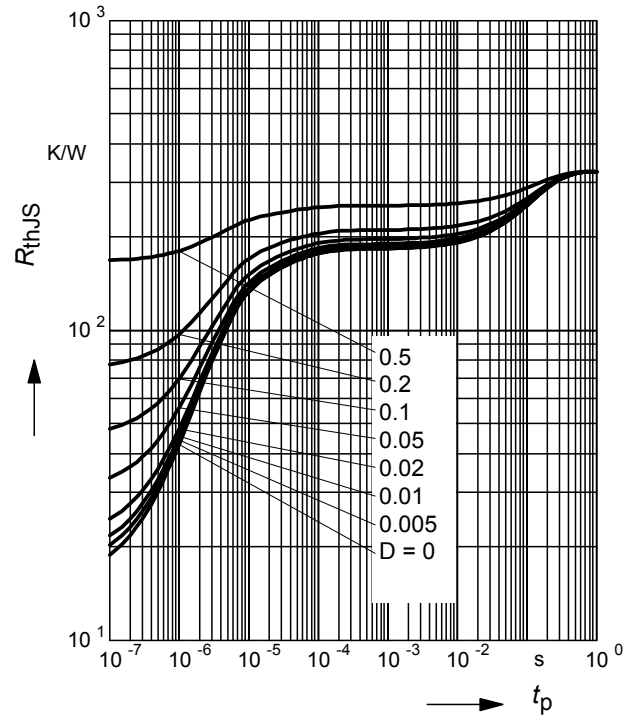
Valid up to 6GHz

For examples and ready to use parameters
please contact your local Infineon Technologies
distributor or sales office to obtain a Infineon
Technologies CD-ROM or see Internet:
<http://www.infineon.com>

Total power dissipation $P_{\text{tot}} = f(T_S)$

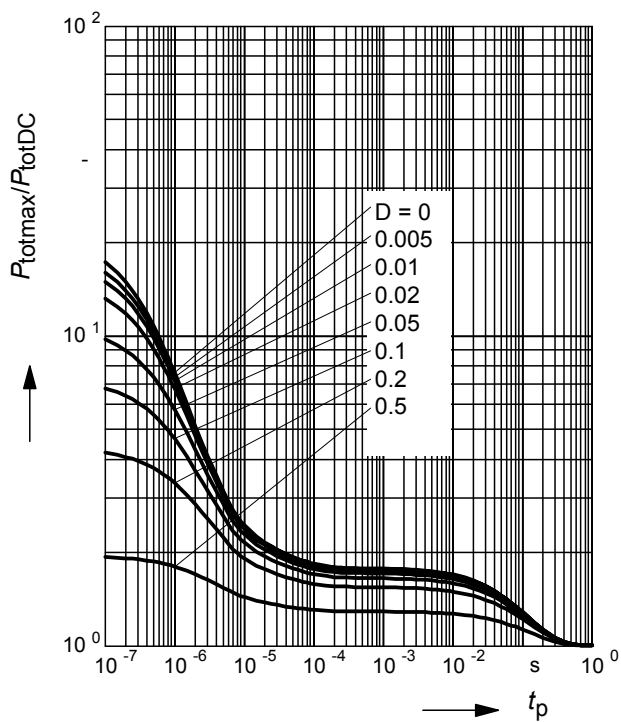


Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$

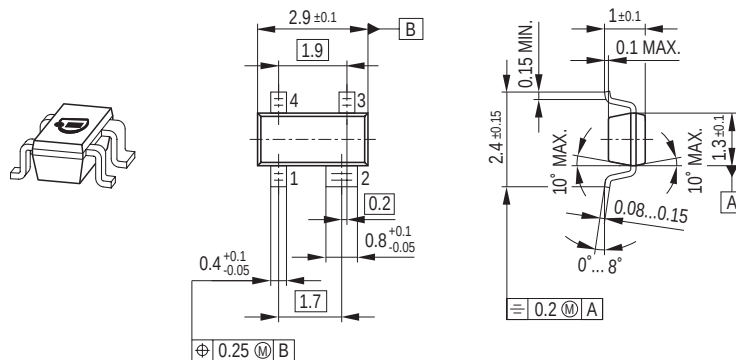


Permissible Pulse Load

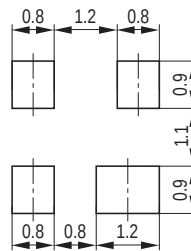
$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$



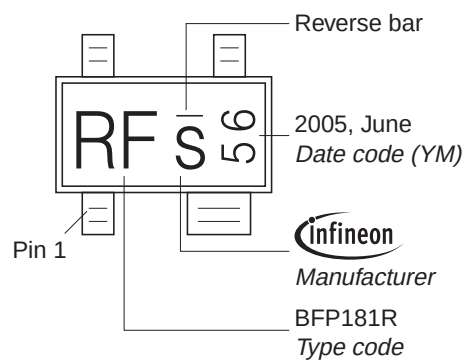
Package Outline



Foot Print

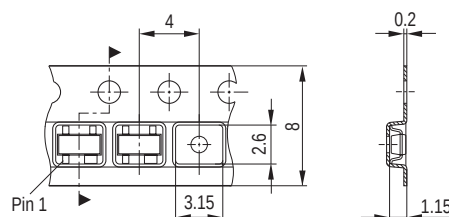


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.